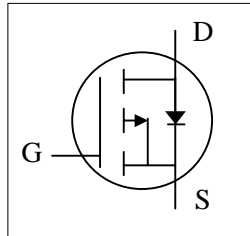




- ▼ Fast Switching Characteristic
- ▼ Lower Gate Charge
- ▼ Small Footprint & Low Profile Package
- ▼ RoHS Compliant & Halogen-Free

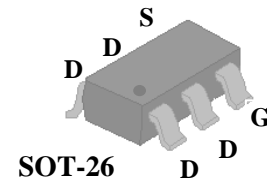


BV_{DSS}	-20V
$R_{DS(ON)}$	37m Ω
I_D^3	-6.2A

Description

AP2613 series are from Advanced Power innovated design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The SOT-26 package is widely used for all commercial-industrial applications.



Absolute Maximum Ratings @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	- 20	V
V_{GS}	Gate-Source Voltage	± 8	V
$I_D@T_A=25^\circ\text{C}$	Drain Current ³ , V_{GS} @ 4.5V	-6.2	A
$I_D@T_A=70^\circ\text{C}$	Drain Current ³ , V_{GS} @ 4.5V	-4.9	A
I_{DM}	Pulsed Drain Current ¹	-24	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation	2	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	62.5	$^\circ\text{C}/\text{W}$



AP2613GY-HF

Electrical Characteristics @T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-20	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =-4.5V, I _D =-4A	-	31	37	mΩ
		V _{GS} =-2.5V, I _D =-3A	-	42	50	mΩ
		V _{GS} =-1.8V, I _D =-1A	-	60	75	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-0.3	-0.7	-1	V
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-4A	-	15	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-16V, V _{GS} =0V	-	-	-10	uA
I _{GSS}	Gate-Source Leakage	V _{GS} = ± 8V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge	I _D =-4A	-	13	21	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-10V	-	1.7	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	4	-	nC
t _{d(on)}	Turn-on Delay Time	V _{DS} =-10V	-	10	-	ns
t _r	Rise Time	I _D =-1A	-	17	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	45	-	ns
t _f	Fall Time	V _{GS} =-5V	-	33	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	1050	1680	pF
C _{oss}	Output Capacitance	V _{DS} =-10V	-	180	-	pF
C _{riss}	Reverse Transfer Capacitance	f=1.0MHz	-	160	-	pF
R _g	Gate Resistance	f=1.0MHz	-	7.3	-	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =-1.2A, V _{GS} =0V	-	-	-1.2	V
t _{rr}	Reverse Recovery Time	I _S =-4A, V _{GS} =0V,	-	27	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt=100A/μs	-	15	-	nC

Notes:

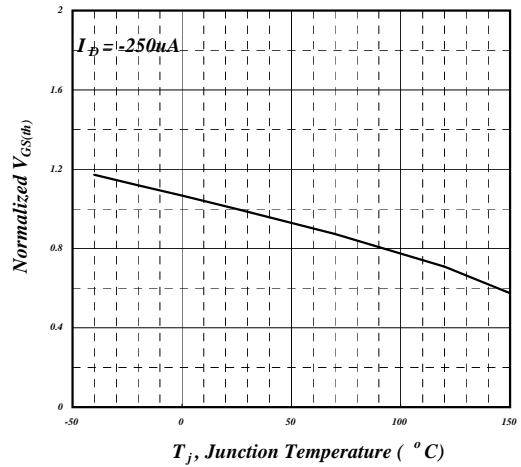
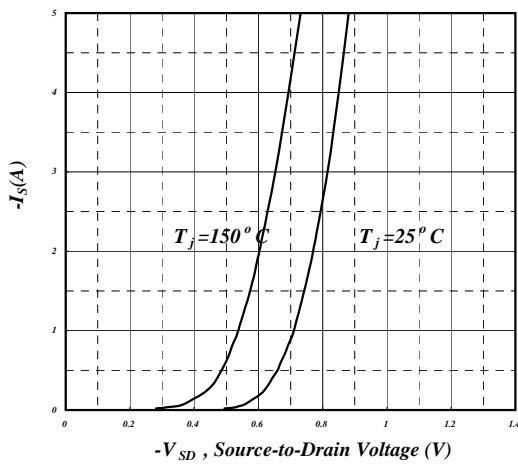
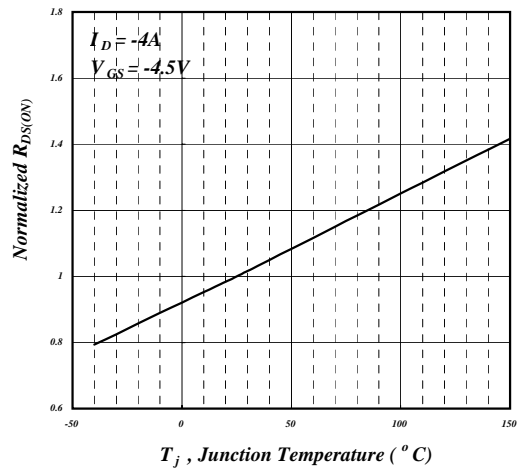
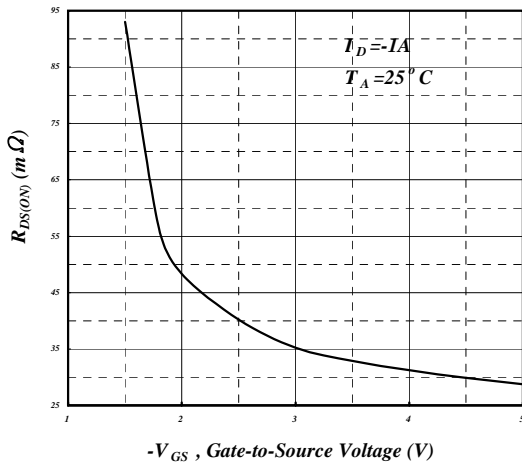
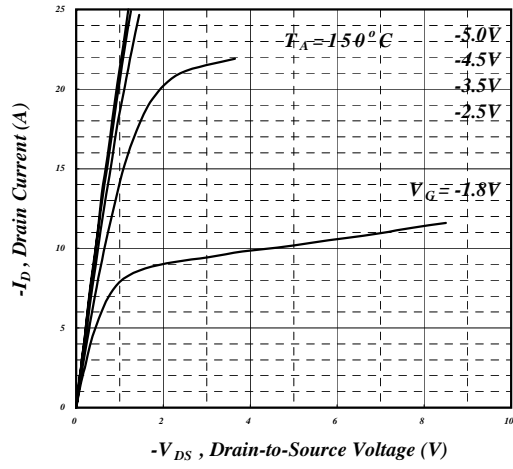
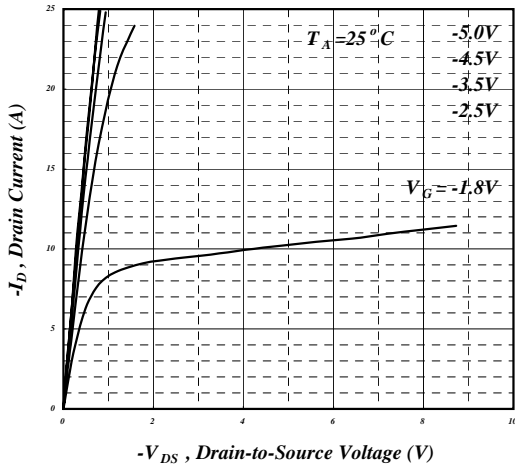
- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board, t ≤ 10s ; 156°C/W when mounted on min. copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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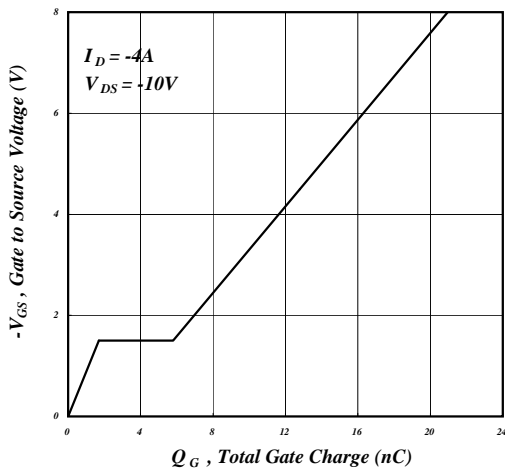


Fig 7. Gate Charge Characteristics

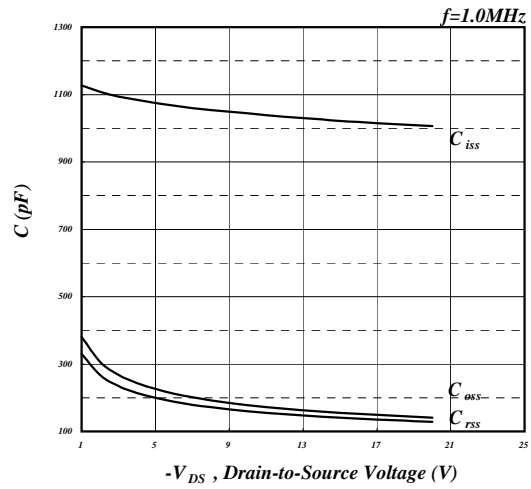


Fig 8. Typical Capacitance Characteristics

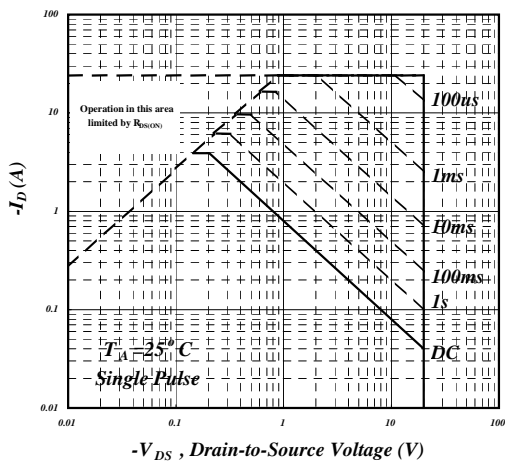


Fig 9. Maximum Safe Operating Area

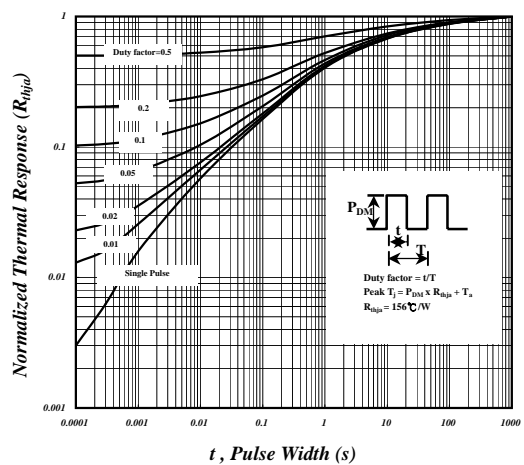


Fig 10. Effective Transient Thermal Impedance

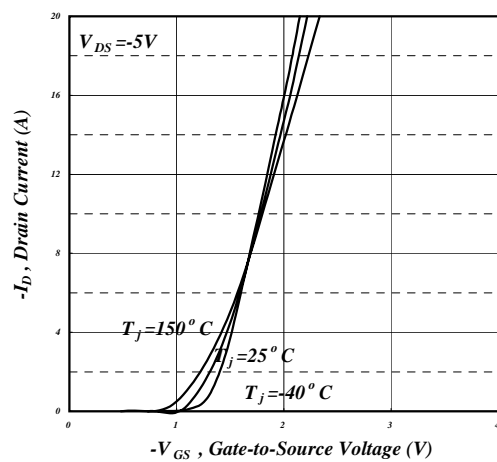


Fig 11. Transfer Characteristics

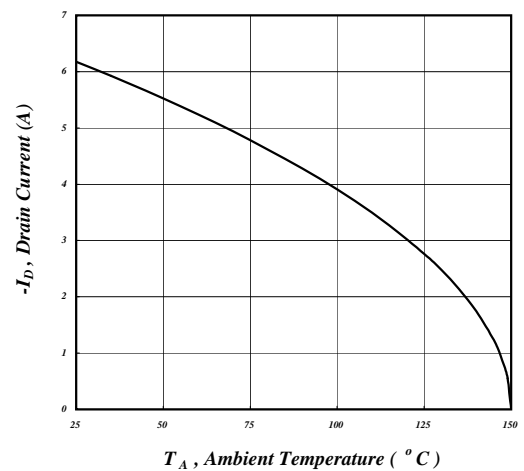


Fig 12. Drain Current v.s. Ambient Temperature



MARKING INFORMATION

